

AMENDMENT UNDER 37 C.F.R. § 1.312  
Serial Number: 10/789,203  
Filing Date: February 27, 2004  
Title: OPERATING A MEMORY DEVICE

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Dkt: 303.356US4

In the Specification

Please amend the paragraph beginning on page 1, line 9 as follows:

This application is related to the following co-pending, commonly assigned U.S. patent applications: "DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR," serial number 08/902,843, now abandoned; "DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE," serial number 08/902,098, now U.S. Patent No. 6,031,263; "CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS," serial number 08/903,453, now abandoned; "SILICON CARBIDE GATE TRANSISTOR AND FABRICATION PROCESS," serial number 08/903,486, now U.S. Patent No. 6,936,849; "TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE," serial number 08/903,452, now abandoned; and "TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE," serial number 08/902,132, now U.S. Patent No. 5,886,368, each of which is filed on the same day as U.S. application, serial no. 08/902,133, filed on 29 July 1997, and each of which disclosure is herein incorporated by reference.